

N-channel 30 V, 6.1 mΩ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

19 September 2014

**Product data sheet** 

### 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

### 2. Features and benefits

- Ultra low Q<sub>G</sub>, Q<sub>GD</sub> and Q<sub>OSS</sub> for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 µA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

### 3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

### 4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	-	-	66	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	47	W

N-channel 30 V, 6.1 mΩ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Tj	junction temperature		-55	-	175	°C
Static char	acteristics	· · ·	I			
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 10	-	6.5	8.35	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 10	-	5.05	6	mΩ
Dynamic cl	haracteristics	· · ·				
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V; Fig. 12; Fig. 13	-	2.1	3.15	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V; Fig. 12; Fig. 13	-	6.8	10.2	nC
Source-dra	in diode					
S	softness factor	$I_{S} = 15 \text{ A}; V_{GS} = 0 \text{ V}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$ $V_{DS} = 15 \text{ V}; \underline{\text{Fig. 16}}$	-	1.3	-	

### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UFA
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

## 6. Ordering information

Table 3. Ordering in	Table 3. Ordering information							
Type number Package								
	Name	Description	Version					
PSMN6R1-30YLD	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669					

## 7. Marking

Table 4. Marking codes		
Type number	Marking code	
PSMN6R1-30YLD	6D130L	
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Product data sheet	19 September 2014	2/13

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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

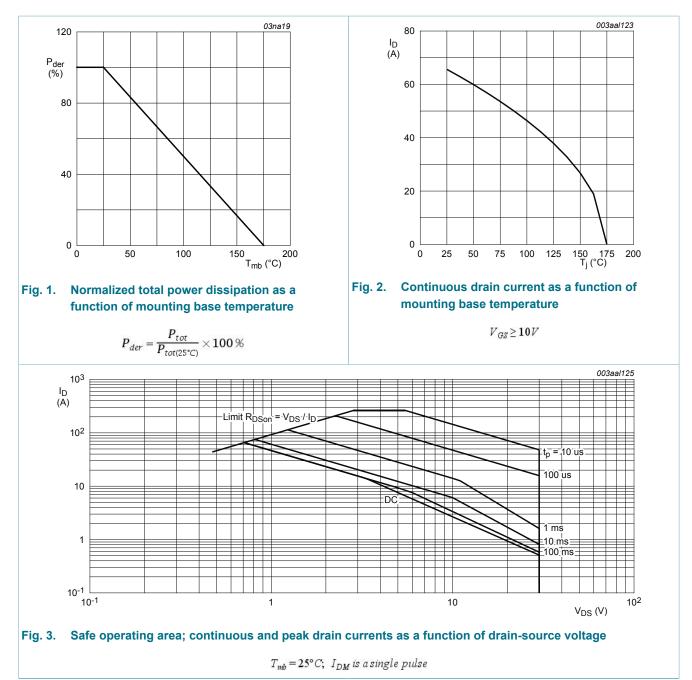
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	30	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	47	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	66	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	46	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	263	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ		250	-	V
Source-drain	diode	·			1	
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	39	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	250	А
Avalanche ru	ıggedness	·			- 1	
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 15 A; $V_{sup} \le 30$ V; $R_{GS}$ = 50 Ω; unclamped; $t_D$ = 145 µs	[1]	-	42	mJ

[1] Protected by 100% test

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### 9. Thermal characteristics

Table 6. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. <u>4</u>	-	3	3.22	K/W

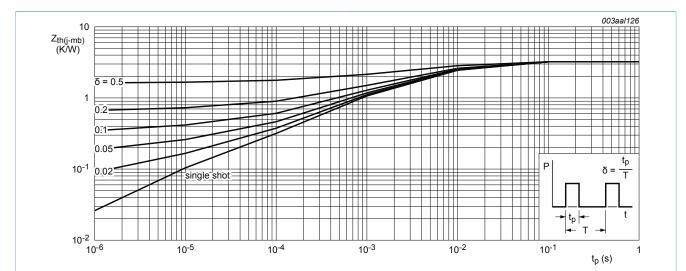
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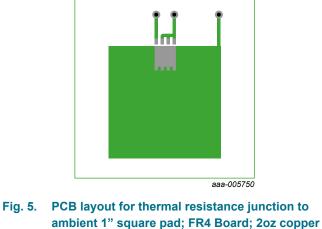
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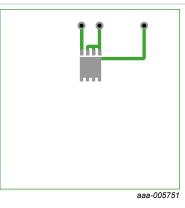
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	<u>Fig. 5</u>	-	50	-	K/W
	from junction to ambient	Fig. 6	-	125	-	K/W









al resistance junction to Id; FR4 Board; 2oz copper Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	octeristics	· · ·	ł			
V <sub>(BR)DSS</sub> drain-s	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	1.2	1.68	2.2	V

PSMN6R1-30YLD

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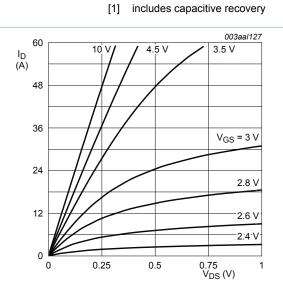
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
ΔV <sub>GS(th)</sub> /ΔT	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-3.9	-	mV/K
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 24 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 10	-	6.5	8.35	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 150 °C; Fig. 11; Fig. 10	-	-	13.8	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 10	-	5.05	6	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 150 °C; Fig. 11; Fig. 10	-	-	9.9	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.44	0.88	Ω
Dynamic cha	aracteristics		I			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13	-	14.2	21.3	nC
		I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; Fig. 12; Fig. 13	-	6.8	10.2	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	13.3	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D$ = 15 A; $V_{DS}$ = 15 V; $V_{GS}$ = 4.5 V;	-	2.2	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	1.3	-	nC
$Q_{GS(th-pl)}$	post-threshold gate- source charge		-	0.9	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.1	3.15	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	2.7	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	817	1225	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	605	908	pF
C <sub>rss</sub>	reverse transfer capacitance		-	62	93	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; R <sub>L</sub> = 1 Ω; V <sub>GS</sub> = 4.5 V;	-	7.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	11	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	9.8	-	ns
t <sub>f</sub>	fall time		-	7.2	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Q <sub>oss</sub>	output charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 15 V; f = 1 MHz; T <sub>j</sub> = 25 °C		-	11.8	-	nC
Source-drai	in diode						
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 10 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 15</u>		-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 15 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;		-	23.8	47.6	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V; <u>Fig. 16</u>	[1]	-	12.6	25.2	nC
t <sub>a</sub>	reverse recovery rise time	-		-	10.3	-	ns
t <sub>b</sub>	reverse recovery fall time			-	13.5	-	ns
S	softness factor			-	1.3	-	





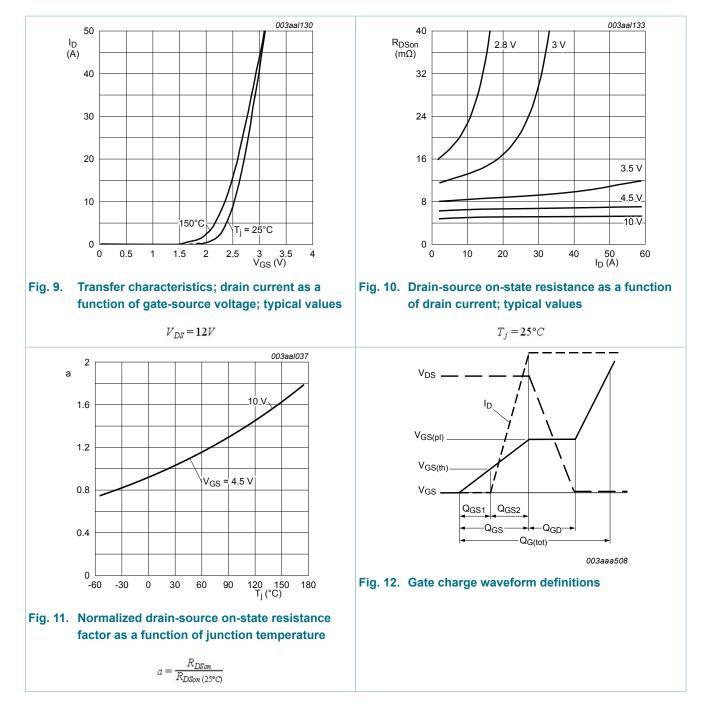
003aal128 30 R<sub>DSon</sub> (mΩ) 25 20 15 10 5 0 12 14 V<sub>GS</sub> (V) 0 2 4 6 8 10 16 Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; \ I_D = 15A$ 

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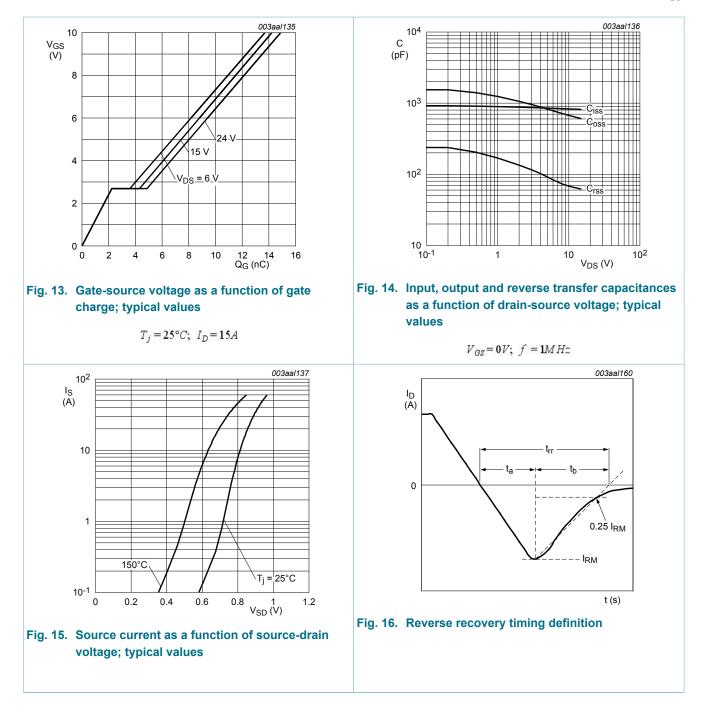
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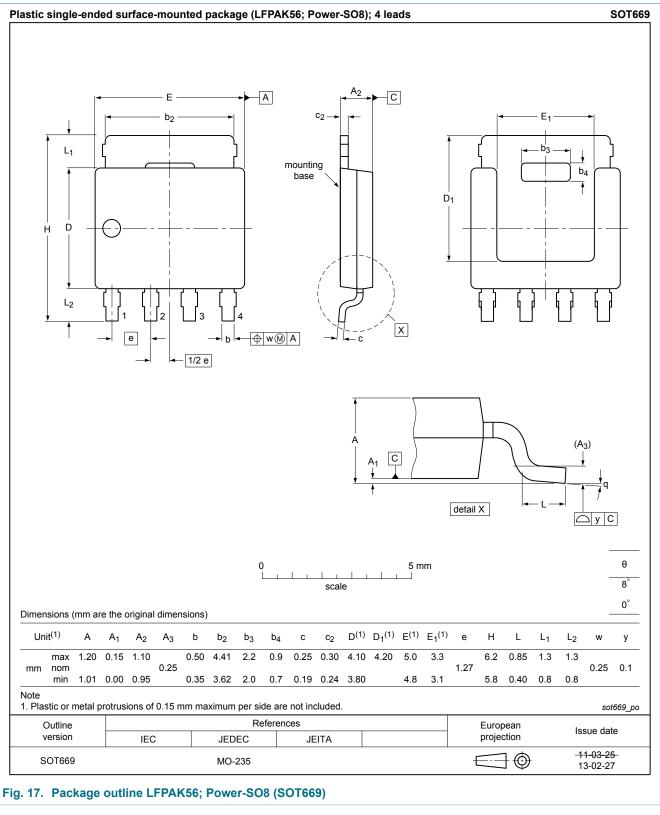
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#### N-channel 30 V, 6.1 mΩ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

### **11. Package outline**



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#### N-channel 30 V, 6.1 mΩ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

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### 13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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